

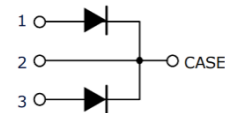


WSRSIC030120NP8-AT

SILICON CARBIDE SCHOTTKY DIODE

Features

- 30A Silicon Carbide Schottky Diode
- Excellent high temperature stability
- Low forward voltage
- High forward surge capability
- 175°C Operating Junction Temperature
- Reduced temperature dependence
- AEC-Q101 qualified



Mechanical Data

- Case: TO-247-3L

Absolute Maximum Ratings (T_c=25°C Unless otherwise specified)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V _{RRM}	1200	V
Surge Peak Reverse Voltage	V _{RSM}	1200	V
DC Blocking Voltage	V _R	1200	V
Maximum Average Forward Rectified Current at T _C =152°C Per leg	I _F	15	A
Maximum Average Forward Rectified Current at T _C =152°C Total device		30	
Surge(Non-Repetitive)Forward Current @ T _p =10ms Half Sine Wave T _C =25°C Per leg	I _{FSM}	140	A
Power Dissipation T _C =25°C	P _{tot}	205	W
Thermal Resistance(between Junction and Case)	R _{θ(J-C)}	0.73 (Typ.)	°C/W
Junction and Storage Temperature	T _J T _{STG}	-55 ~ +175	°C

Electronics Characteristics (T_c=25°C Unless otherwise specified&Per Leg)

Parameter	Symbol	Typ.	Max.	Unit
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SILICON CARBIDE SCHOTTKY DIODE

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Maximum Instantaneous Forward Voltage @ $I_F=15A$ $T_J=25^\circ C$	V_F	1.43	1.8	V
Maximum Instantaneous Forward Voltage @ $I_F=15A$ $T_J=175^\circ C$		2	/	
Total Capacitance @ $f=1MHz$ $T_J=25^\circ C$ $V_R=0V$	C	1015	/	pF
Total Capacitance @ $f=1MHz$ $T_J=25^\circ C$ $V_R=400V$		75		
Total Capacitance @ $f=1MHz$ $T_J=25^\circ C$ $V_R=800V$		55		
Total Capacitive Charge @ $V_R=800V$	Q_C	62	/	nC
Reverse leakage current @ $V_R=1200V$ $T_J=25^\circ C$	I_R	3	50	μA
Reverse leakage current @ $V_R=1200V$ $T_J=175^\circ C$		15	/	

Typical Characteristics

Fig.1-Forward Characteristics

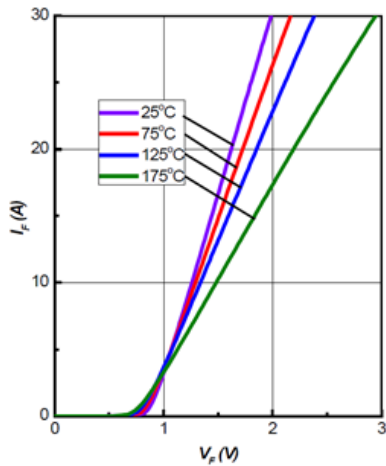


Fig.2-Reverse Characteristics

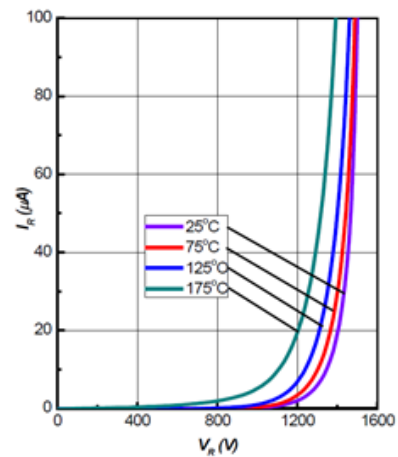


Fig.3-Total Capacitance Charge VS Reverse Voltage

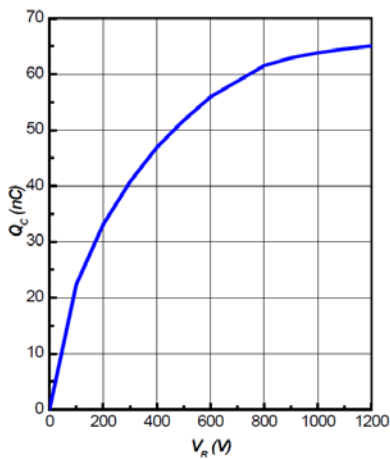
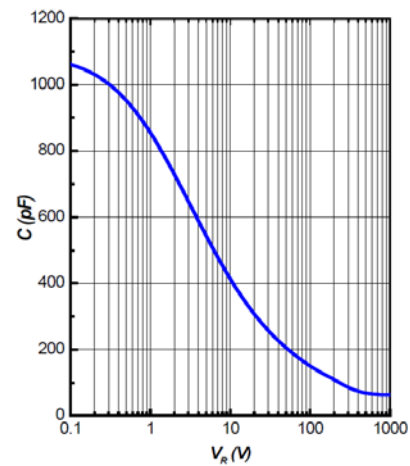
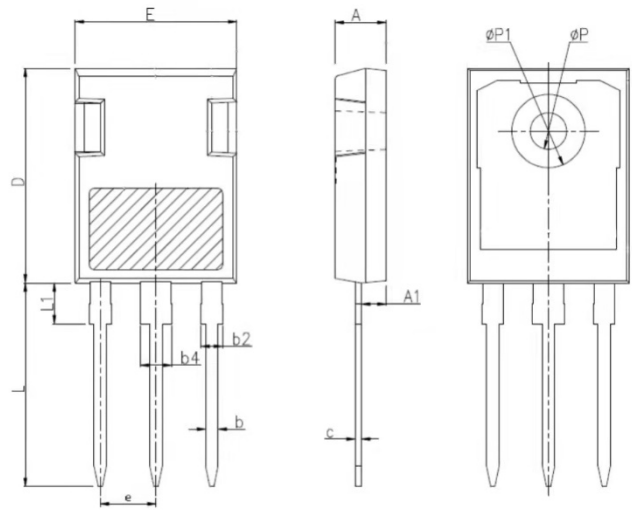


Fig.4-Capacitance VS Reverse Voltage

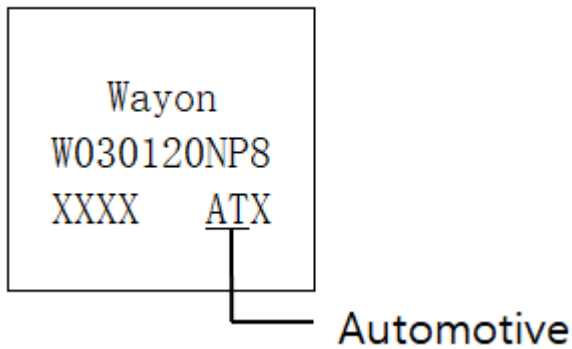


Outline Drawing

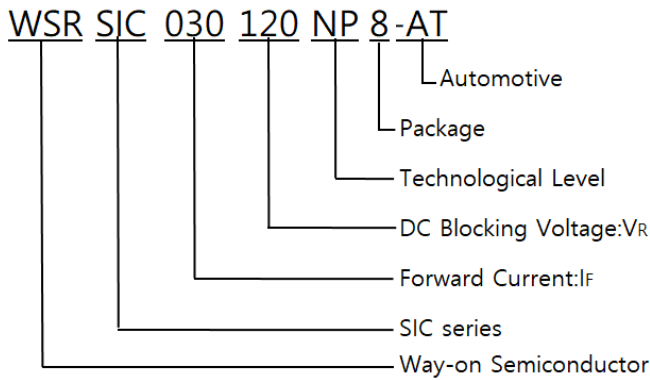
SYMBOL	MM		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
b	1.10	1.20	1.36
b2	1.90	2.00	2.21
b4	2.90	3.01	3.21
c	0.50	0.60	0.75
D	20.70	21.00	21.30
E	15.50	15.80	16.10
e	5.44BSC		
L	19.62	19.92	20.22
L1	/	/	4.30
ΦP1	/	/	7.30
ΦP	3.40	3.60	3.80



Marking Information



Part Number System



Package Information

Quantity per tube: 30pcs

Contact Information

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For additional information, please contact your local Sales Representative.

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*Specifications are subject to change without notice.
The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.
Users should verify actual device performance in their specific applications.*